BC337
NPN general purpose transistor

Product specification
Supersedes data of 1997 Mar 10
FEATURES

- High current (max. 500 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- General purpose switching and amplification, e.g. driver and output stages of audio amplifiers.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.
PNP complement: BC327.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

<table>
<thead>
<tr>
<th>SYMBOL</th>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>MIN.</th>
<th>MAX.</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>V_{CBO}</td>
<td>collector-base voltage</td>
<td>open emitter</td>
<td>–</td>
<td>50</td>
<td>V</td>
</tr>
<tr>
<td>V_{CEO}</td>
<td>collector-emitter voltage</td>
<td>open base</td>
<td>–</td>
<td>45</td>
<td>V</td>
</tr>
<tr>
<td>V_{EBO}</td>
<td>emitter-base voltage</td>
<td>open collector</td>
<td>–</td>
<td>5</td>
<td>V</td>
</tr>
<tr>
<td>I_C</td>
<td>collector current (DC)</td>
<td></td>
<td>–</td>
<td>500</td>
<td>mA</td>
</tr>
<tr>
<td>I_{CM}</td>
<td>peak collector current</td>
<td></td>
<td>–</td>
<td>1</td>
<td>A</td>
</tr>
<tr>
<td>I_{BM}</td>
<td>peak base current</td>
<td></td>
<td>–</td>
<td>200</td>
<td>mA</td>
</tr>
<tr>
<td>P_{tot}</td>
<td>total power dissipation</td>
<td>T_{amb} ≤ 25 °C; note 1</td>
<td>–</td>
<td>625</td>
<td>mW</td>
</tr>
<tr>
<td>T_{stg}</td>
<td>storage temperature</td>
<td></td>
<td>–65</td>
<td>+150</td>
<td>°C</td>
</tr>
<tr>
<td>T_{j}</td>
<td>junction temperature</td>
<td></td>
<td>–</td>
<td>150</td>
<td>°C</td>
</tr>
<tr>
<td>T_{amb}</td>
<td>operating ambient temperature</td>
<td></td>
<td>–65</td>
<td>+150</td>
<td>°C</td>
</tr>
</tbody>
</table>

Note

1. Transistor mounted on an FR4 printed-circuit board.
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THERMAL CHARACTERISTICS

<table>
<thead>
<tr>
<th>SYMBOL</th>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>VALUE</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>$R_{th,j-a}$</td>
<td>thermal resistance from junction to ambient</td>
<td>note 1</td>
<td>0.2</td>
<td>K/mW</td>
</tr>
</tbody>
</table>

Note
1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_J = 25 \, ^\circ C$ unless otherwise specified.

<table>
<thead>
<tr>
<th>SYMBOL</th>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>MIN.</th>
<th>TYP.</th>
<th>MAX.</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>$I_{CBO}$</td>
<td>collector cut-off current</td>
<td>$I_E = 0; V_CB = 20 , V$</td>
<td>–</td>
<td>–</td>
<td>100</td>
<td>nA</td>
</tr>
<tr>
<td></td>
<td></td>
<td>$I_E = 0; V_CB = 20 , V; T_J = 150 , ^\circ C$</td>
<td>–</td>
<td>–</td>
<td>5</td>
<td>µA</td>
</tr>
<tr>
<td>$I_{EBO}$</td>
<td>emitter cut-off current</td>
<td>$I_C = 0; V_EB = 5 , V$</td>
<td>–</td>
<td>–</td>
<td>100</td>
<td>nA</td>
</tr>
<tr>
<td>$h_{FE}$</td>
<td>DC current gain</td>
<td>$I_C = 100 , mA; V_CE = 1 , V$; see Figs 2, 3 and 4</td>
<td>100</td>
<td>–</td>
<td>600</td>
<td>–</td>
</tr>
<tr>
<td></td>
<td></td>
<td>BC337</td>
<td>100</td>
<td>–</td>
<td>250</td>
<td>–</td>
</tr>
<tr>
<td></td>
<td></td>
<td>BC337-16</td>
<td>160</td>
<td>–</td>
<td>400</td>
<td>–</td>
</tr>
<tr>
<td></td>
<td></td>
<td>BC337-25</td>
<td>250</td>
<td>–</td>
<td>600</td>
<td>–</td>
</tr>
<tr>
<td></td>
<td></td>
<td>BC337-40</td>
<td>–</td>
<td>–</td>
<td>–</td>
<td>–</td>
</tr>
<tr>
<td></td>
<td>DC current gain</td>
<td>$I_C = 500 , mA; V_CE = 1 , V$; see Figs 2, 3 and 4</td>
<td>40</td>
<td>–</td>
<td>–</td>
<td>–</td>
</tr>
<tr>
<td>$V_{CE_{sat}}$</td>
<td>collector-emitter saturation voltage</td>
<td>$I_C = 500 , mA; I_B = 50 , mA$</td>
<td>–</td>
<td>–</td>
<td>700</td>
<td>mV</td>
</tr>
<tr>
<td>$V_{BE}$</td>
<td>base-emitter voltage</td>
<td>$I_C = 500 , mA; V_CE = 1 , V$; note 1</td>
<td>–</td>
<td>–</td>
<td>1.2</td>
<td>V</td>
</tr>
<tr>
<td>$C_c$</td>
<td>collector capacitance</td>
<td>$I_E = I_B = 0; V_CB = 10 , V; f = 1 , MHz$</td>
<td>–</td>
<td>5</td>
<td>–</td>
<td>pF</td>
</tr>
<tr>
<td>$f_T$</td>
<td>transition frequency</td>
<td>$I_C = 10 , mA; V_CE = 5 , V; f = 100 , MHz$</td>
<td>100</td>
<td>–</td>
<td>–</td>
<td>MHz</td>
</tr>
</tbody>
</table>

Note
1. $V_{BE}$ decreases by about 2 mV/K with increasing temperature.
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Fig.2 DC current gain; typical values.

Fig.3 DC current gain; typical values.
Fig.4  DC current gain; typical values.
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads  
SOT54

DIMENSIONS (mm are the original dimensions)

<table>
<thead>
<tr>
<th>UNIT</th>
<th>A</th>
<th>b</th>
<th>b1</th>
<th>c</th>
<th>D</th>
<th>d</th>
<th>E</th>
<th>e</th>
<th>e1</th>
<th>L</th>
<th>L1(1)</th>
</tr>
</thead>
<tbody>
<tr>
<td>mm</td>
<td>5.2</td>
<td>0.48</td>
<td>0.66</td>
<td>0.45</td>
<td>4.8</td>
<td>1.7</td>
<td>4.2</td>
<td>2.54</td>
<td>1.27</td>
<td>14.5</td>
<td>2.5</td>
</tr>
<tr>
<td>5.0</td>
<td>0.40</td>
<td>0.56</td>
<td>0.40</td>
<td>4.4</td>
<td>4.4</td>
<td>1.4</td>
<td>3.6</td>
<td></td>
<td></td>
<td>12.7</td>
<td></td>
</tr>
</tbody>
</table>

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.
DEFINITIONS

<table>
<thead>
<tr>
<th>Data Sheet Status</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>Objective specification</td>
<td>This data sheet contains target or goal specifications for product development.</td>
</tr>
<tr>
<td>Preliminary specification</td>
<td>This data sheet contains preliminary data; supplementary data may be published later.</td>
</tr>
<tr>
<td>Product specification</td>
<td>This data sheet contains final product specifications.</td>
</tr>
</tbody>
</table>

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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